



STP80NF12

N-channel 120V - 0.013Ω - 80A - TO-220
STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D
STP80NF12	120V	<0.018Ω	80A ⁽¹⁾

1. Limited by package

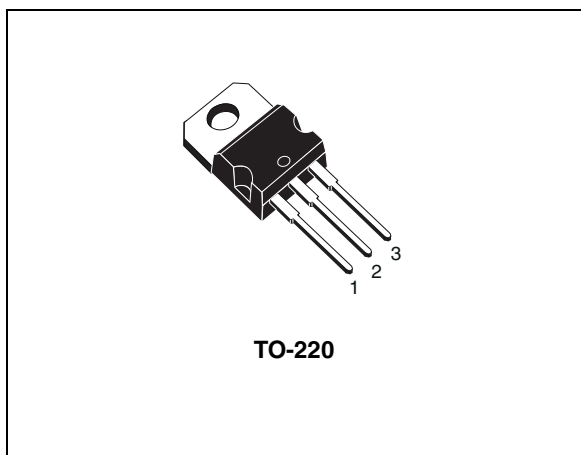
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

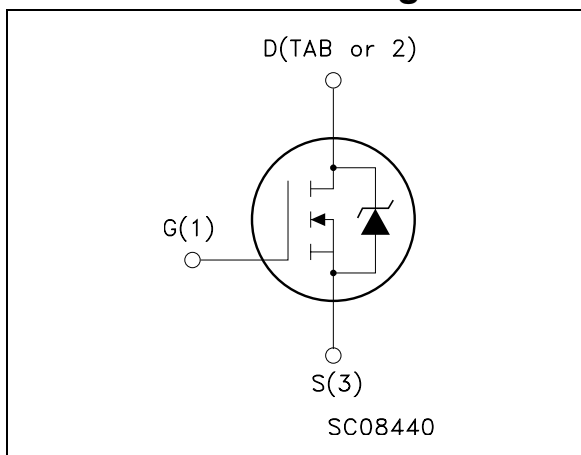
This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

Application

- Switching application



Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STP80NF12	P80NF12	TO-220	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	120	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	60	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2.0	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	10	V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Limited by Package
2. Pulse width limited by safe operating area
3. Starting $T_J = 25^\circ\text{C}$, $I_D = 40\text{A}$, $V_{DD} = 45\text{V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case Max	0.5	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient Max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	120			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating} @ 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 40A$		0.013	0.018	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 40A$		80		S
C_{iss}	Input capacitance	$V_{DS} = 25V, f = 1 \text{ MHz},$ $V_{GS} = 0$		4300		pF
C_{oss}	Output capacitance			600		pF
C_{rss}	Reverse transfer capacitance			230		pF
Q_g	Total gate charge	$V_{DD} = 80V, I_D = 80A$ $V_{GS} = 10V$		140	189	nC
Q_{gs}	Gate-source charge			23		nC
Q_{gd}	Gate-drain charge			51		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50 \text{ V}, I_D = 40A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ <i>Figure 12 on page 8</i>		40		ns
t_r	Rise time			145		ns
$t_{d(off)}$	Turn-off delay time			134		ns
t_f	Fall time			115		ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=80A, V_{GS}=0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD}=80A,$		155		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100A/\mu s,$		0.85		μC
I_{RRM}	Reverse recovery current	$V_{DD}=35V, T_J = 150^\circ C$		11		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

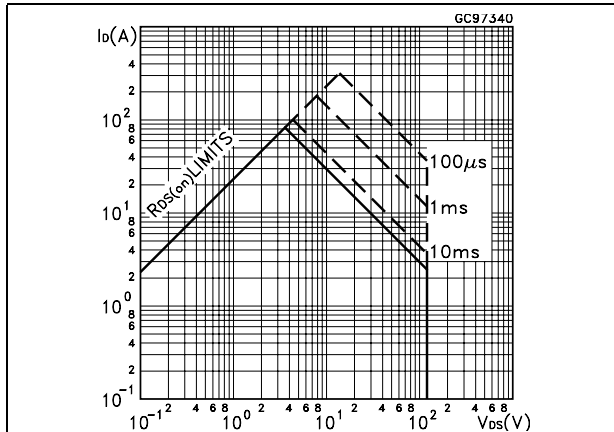


Figure 2. Thermal impedance

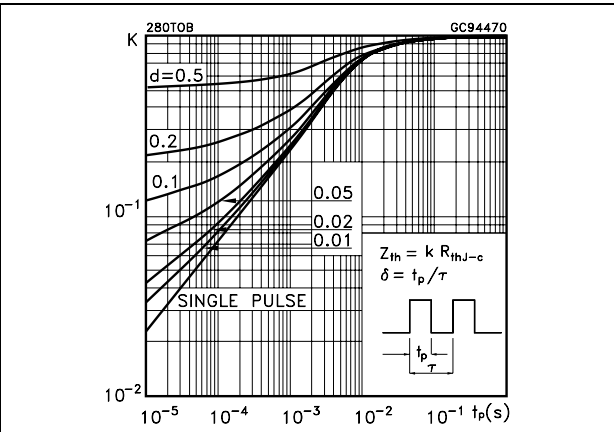


Figure 3. Output characteristics

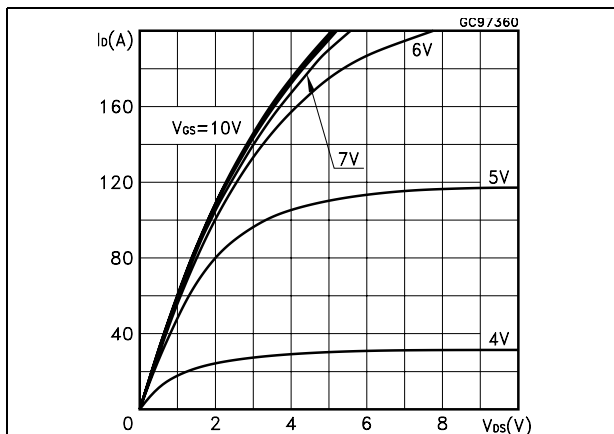


Figure 4. Transfer characteristics

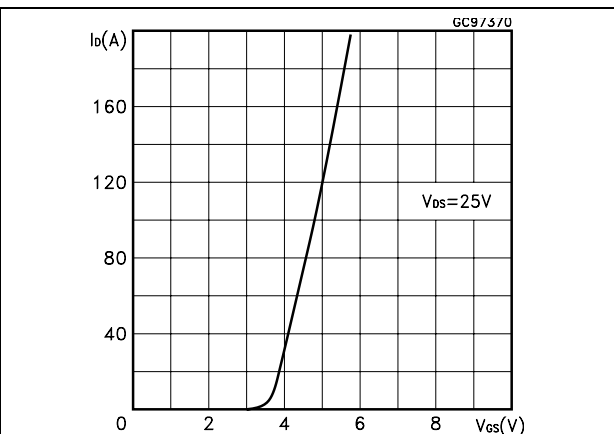


Figure 5. Normalized $B_{V_{DS}}$ vs. temperature

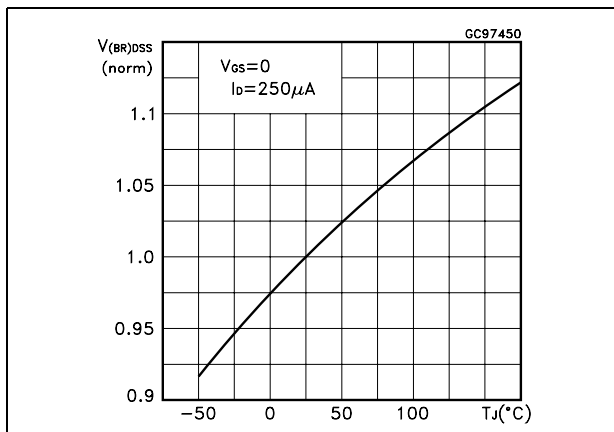


Figure 6. Static drain-source on resistance

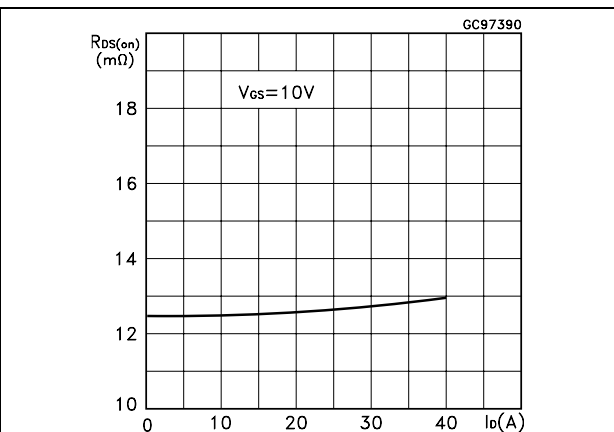


Figure 7. Gate charge vs. gate-source voltage Figure 8. Capacitance variations

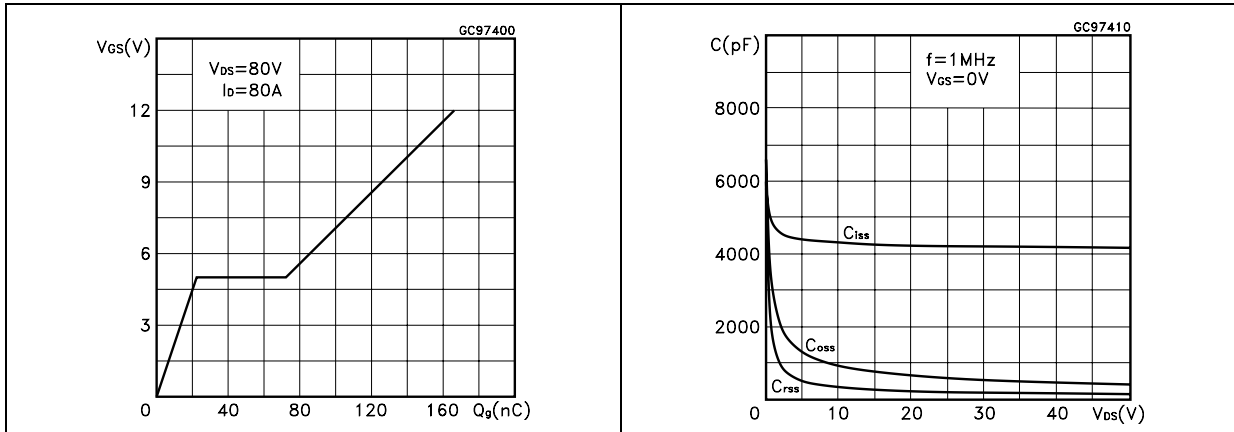


Figure 9. Normalized gate threshold voltage vs. temperature Figure 10. Normalized on resistance vs. temperature

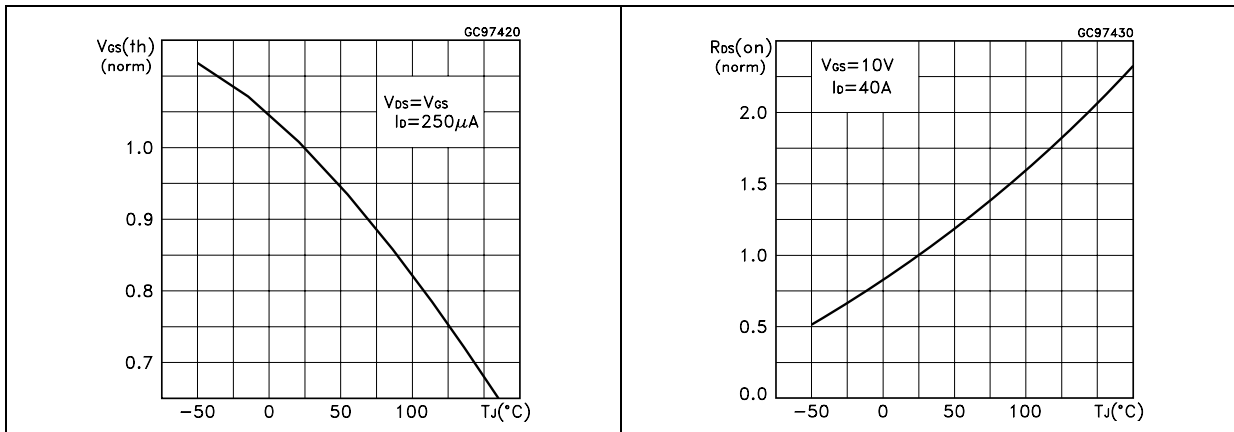
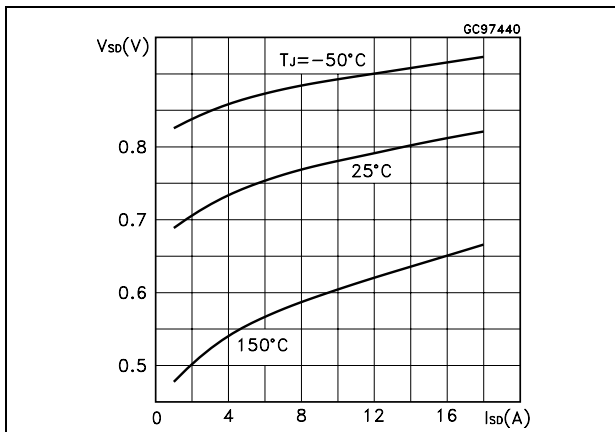


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

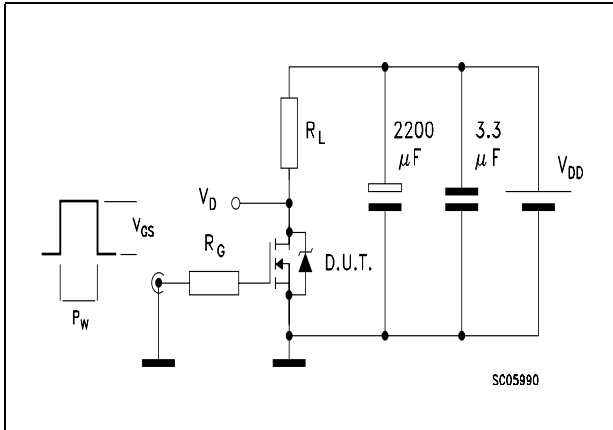


Figure 13. Gate charge test circuit

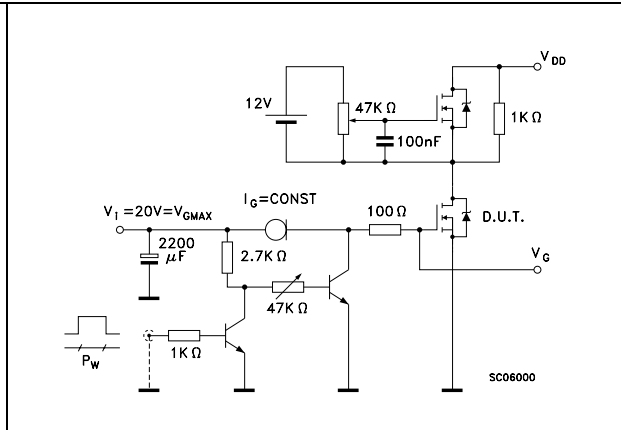


Figure 14. Test circuit for inductive load switching and diode recovery times

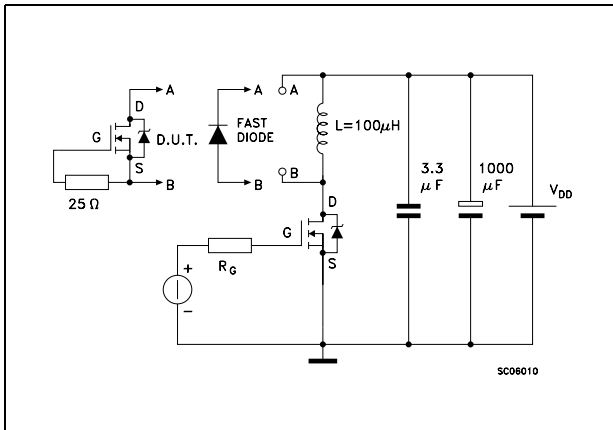


Figure 15. Unclamped Inductive load test circuit

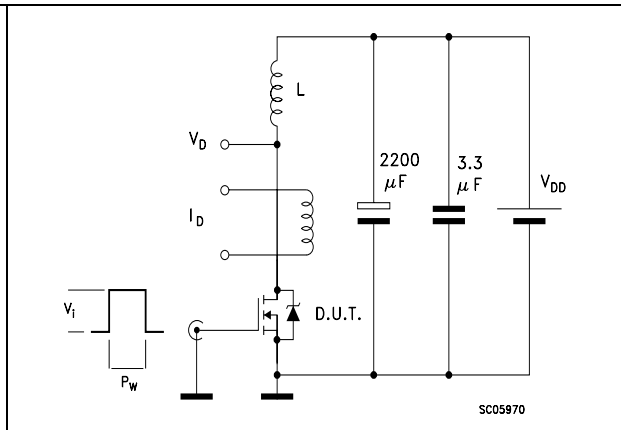
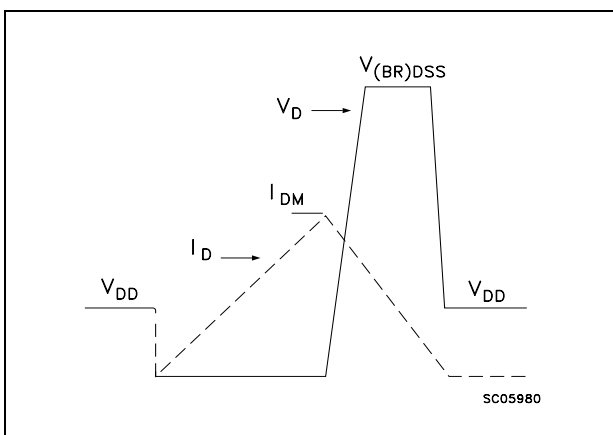


Figure 16. Unclamped inductive waveform

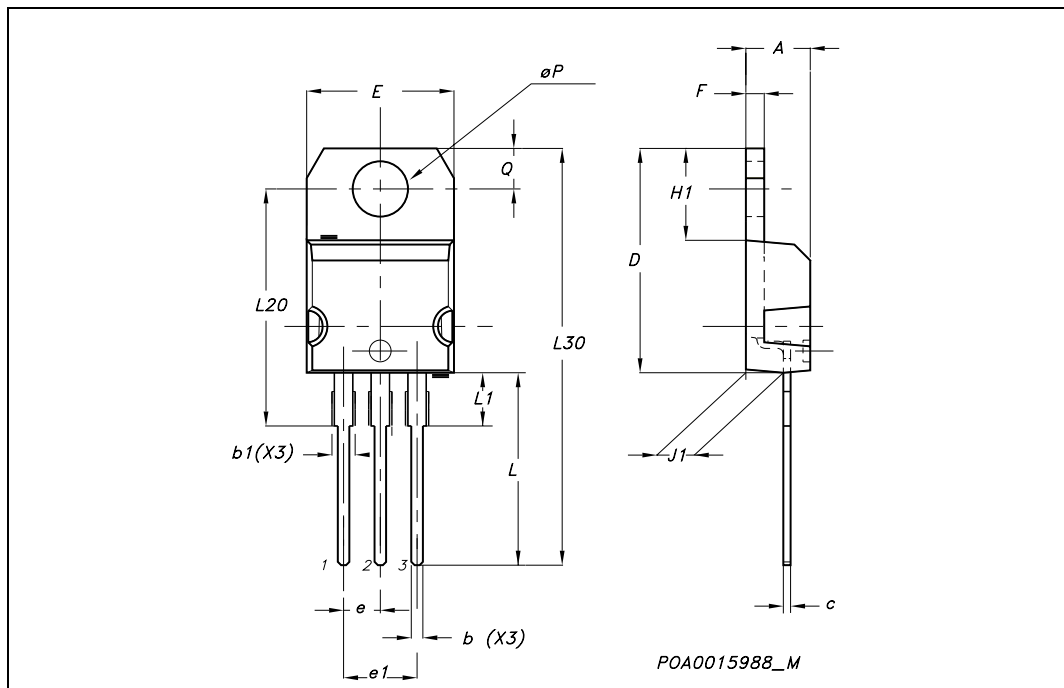


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



5 Revision history

Table 7. Revision history

Date	Revision	Changes
21-Jun-2004	2	Preliminary version
24-Jul-2006	3	The document has been reformatted, SOA updated
31-Jan-2007	4	Typo mistake on Table 1 .
10-Apr-2007	5	Typo mistake on Table 1 and Table 2
19-Apr-2007	6	Corrected value on Table 3

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